

L Number	Hits	Search Text	DB	Time stamp
304	2	westra.in. and silicon and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 08:21
297	101	westra.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 08:21
	2	("6008128").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 09:09
	576	(359/223).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:14
	255	(359/298).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:14
	505	(359/838).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:14
	88	(205/116).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:15
	135	((359/223).CCLS.) and silicon\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 09:20
	85	((359/298).CCLS.) and silicon\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:21
	66	((359/838).CCLS.) and silicon\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:30

	8	((205/116).CCLS.) and silicon\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:33
	421	silicon and mirror and bulk and monolith\$ and crystal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:43
	46	(silicon and mirror and bulk and monolith\$ and crystal\$4) and inlet and outlet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:37
	31	silicon and mirror and bulk and monolith\$ and (crystal\$4 adj plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 10:51
	89	(single adj crystal adj silicon) and mirror and (crystal\$4 adj plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 11:08
	692	(single adj crystal adj silicon) and mirror and plane and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 11:43
	309	((single adj crystal adj silicon) and mirror and plane and etch\$3) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 11:09
	101	(((single adj crystal adj silicon) and mirror and plane and etch\$3) and anisotrop\$) and fiber and optic\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 11:10
	121	(single and crystal and silicon) and mirror and plane and etch\$3 and anisotrop\$ and fiber and optic\$4 and internal\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:11
	256	single and crystal\$4 and silicon and mirror and etch\$3 and stripe and intersect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:25

	118	(singl and crystal\$4 and silicon and mirror and etch\$3 and strip and intersect\$4) and internal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 11:58
	373	(single near crystal\$4 near silicon) with mirror	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 12:05
	39	((single near crystal\$4 near silicon) with mirror) and (fiber near optic\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 12:06
	3645	digital and mirror and device and silicon and crystal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:12
	168	(digital and mirror and device and silicon and crystal\$4) and bulk and monolith\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:12
	341	silicon and mirror and etch\$3 and stripe and intersect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:36
	2259	silicon and mirror and pattern\$3 and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 14:37
	403	(single adj crystal\$4 adj silicon) and mirror and pattern\$3 and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:20
	0	(bulk with (single adj crystal\$4 adj silicon)) and (mirror near pattern\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:22
	20	silicon and (mirror near pattern\$3) and (anisotrop\$ near etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:34

	16	silicon and ((mirror near pattern\$3) with array\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:39
	2585	(mirror with array\$) and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:16
	9	(mirror with array\$) and (bulk with single with crystal\$4 with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:43
	2	((mirror with array\$) and silicon) and anisotrop\$ and (bulk near crystal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 15:44
	2	monolithic adj bulk adj crystal adj silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:17
	2	monolithic with bulk with crystal with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:17
	1586	monolithic and bulk and crystal and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:18
	25	(monolithic and bulk and crystal and silicon) and (crystalline near plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:19
	362	(monolithic and bulk and crystal and silicon) and (crystalline and plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:20
	4	((monolithic and bulk and crystal and silicon) and (crystalline and plane)) and (micro?mirror or (micro adj mirror))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:20

	109	((monolithic and bulk and crystal and silicon) and (crystallin and plane)) and mirror	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:41
	4	silicon near mirror near array	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:42
	1415	digital near (micromirror or micro?mirror or (micro adj mirror)) near device	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 16:43
	350	(digital near (micromirror or micro?mirror or (micro adj mirror)) near device) and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 17:12
	16	(digital near (micromirror or micro?mirror or (micro adj mirror)) near device) and (single adj crystal adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 17:14
	3991	(mirror or reflect\$) and (single adj crystal adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 17:16
	240	((mirror or reflect\$) and (single adj crystal adj silicon)) and bulk and monolith\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 17:42
	148	anisotrop\$ with silicon with array with etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 17:43
	226	(anisotrop\$ with silicon with process\$) and (mirror or reflector)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 18:38
	25	silicon and mirror and passage and (crystalline adj plane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 18:42

	42	(monolithic and bulk and crystal and silicon) and (mirror or reflector) and crystalline and plan and intersect\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/17 18:44
	606	(359/223).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:15
	290	(359/298).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:28
	553	(359/838).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:27
	88	(205/116).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:27
	42	((359/223).CCLS.) and (mirror or reflector) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:28
	23	((359/298).CCLS.) and (mirror or reflector) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:52
	15	((359/838).CCLS.) and (mirror or reflector) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:54
	1	((205/116).CCLS.) and (mirror or reflector) and anisotrop\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/07 17:56
	244	silicon and ((mirror or reflector) with anisotrop\$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 08:20